

DIGITRON SEMICONDUCTORS

MCR70-0A SERIES
MCR71 SERIES

35 AMP SILICON CONTROLLED RECTIFIER
55 AMP SILICON CONTROLLED RECTIFIER

Available Non-RoHS (standard) or RoHS compliant (add PBF suffix).
Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
		MCR70-0A	MCR71	
Repetitive peak forward or reverse blocking voltage ⁽¹⁾ MCR70-()A MCR71	V_{DRM}/V_{RRM}	2	50	Volts
		3	100	
		6	400	
Peak discharge current ⁽²⁾	I_{TM}	850	1700	Amps
On-state current ($T_C \leq 75^\circ\text{C}$)	$I_{T(RMS)}$	35	55	Amps
	$I_{T(AV)}$	22	35	
Peak non-repetitive surge current (1/2 cycle, sine wave, 60Hz, $T_J = 125^\circ\text{C}$)	I_{TSM}	350	550	Amps
Circuit fusing ($t = 8.3$ ms)	I^2t	510	1255	A^2s
Critical rate of rise of current ⁽³⁾	di/dt	100	200	$\text{A}/\mu\text{s}$
Forward peak gate power ($t \leq 20\mu\text{s}$)	P_{GM}	20		Watts
Forward average gate power	$P_{G(AV)}$	0.5		Watts
Forward peak gate current ($t \leq 20\mu\text{s}$)	I_{GM}	2		Amps
Operating junction storage temperature range	T_J	-40 to +125		$^\circ\text{C}$
Storage temperature range	T_{stg}	-40 to +150		$^\circ\text{C}$
Mounting torque	-	30		In. lb.

1. The rated voltage can be applied over the rated operating junction temperatures without incurring damage. Ratings apply for shorted-open or shorted-gate conditions or negative voltage on the gate. Devices should not be tested for blocking capability in a manner such that the voltage supplied exceeds the rated blocking voltages.
2. Rating is for $t_w = 1\text{ms}$.
3. Test conditions: $I_G = 150\text{mA}$, $V_D = \text{Rated } V_{DRM}$, $I_{TM} = \text{Rated value}$, $T_J = 125^\circ\text{C}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal resistance, junction to case	$R_{\theta JC}$	1	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Peak forward or reverse blocking current (rated V_{DRM} or V_{RRM}) ($T_J = 25^\circ\text{C}$) ($T_J = 125^\circ\text{C}$)	I_{DRM}, I_{RRM}	-	-	10	μA mA
On-state voltage ⁽¹⁾ ($I_{TM} = 70\text{A}$) ($I_{TM} = 175\text{A}$) ($I_{TM} = 850\text{A}$, $t_w = 1\text{ms}$) ⁽²⁾ ($I_{TM} = 1700\text{A}$, $t_w = 1\text{ms}$) ⁽²⁾	V_{TM}	-	1.5	1.85	Volts
MCR70 SERIES		-	1.7	2.1	
MCR71 SERIES		-	6	-	
MCR70 SERIES		-	7	-	
Gate trigger current (continuous dc) ($V_D = 12\text{V}$, $R_L = 100\Omega$)	I_{GT}	2	10	30	mA
Gate trigger voltage (continuous dc) ($V_D = 12\text{V}$, $R_L = 100\Omega$) ($V_D = \text{rated } V_{DRM}$, $R_L = 1\text{k}\Omega$, $T_J = 125^\circ\text{C}$)	V_{GT}	- 0.2	1 -	1.5 -	Volts
Holding current ($I_{TM} = 0.5\text{A}$, gate open)	I_H	3	15	50	mA
Latching current ($V_D = 12\text{Vdc}$, $I_G = 150\text{mA}$, $t_r \leq 50\mu\text{s}$)	I_L	-	30	60	mA
Critical rate of rise off state voltage ($V_D = \text{rated } V_{DRM}$, gate open, exponential waveform, $T_C = 125^\circ\text{C}$)	dv/dt	10	-	-	$\text{V}/\mu\text{s}$

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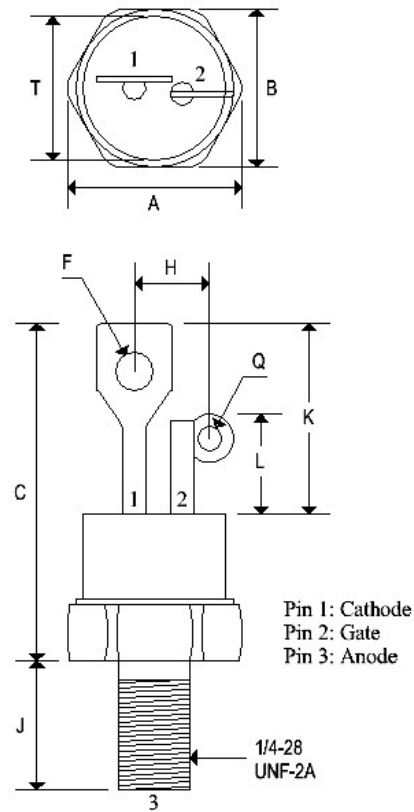
Turn on time ⁽³⁾ ($V_D = \text{rated } V_{DRM}, I_G = 150\text{mA}$) ($I_{TM} = 70\text{A, peak}$) ($I_{TM} = 110\text{A, peak}$)	MCR70 SERIES MCR71 SERIES	t_{on}	- -	1 1.2	μS
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Notes:

1. Duty cycle $\leq 1\%$. Pulse width $\leq 300\mu\text{s}$.
2. Characteristic applies for $t_w = 1\text{ms}$. t_w is defined as 5 time constants of an exponentially decaying current pulse.
3. The gate controlled turn-on time in a crowbar circuit will be influenced by the circuit inductance.

MECHANICAL CHARACTERISTICS

Case	TO-48
Marking	Body painted, alpha-numeric
Polarity	Cathode is stud



	TO-48			
	Inches		Millimeters	
	Min	Max	Min	Max
A	0.604	0.614	15.340	15.600
B	0.551	0.559	14.000	14.200
C	1.050	1.190	2.670	30.230
F	0.135	0.160	3.430	4.060
H	-	0.265	-	6.730
J	0.420	0.455	10.670	11.560
K	0.620	0.670	15.750	17.020
L	0.300	0.350	7.620	8.890
Q	0.055	0.085	1.400	2.160
T	0.501	0.505	12.730	12.830

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FIGURE 1 - PEAK CAPACITOR DISCHARGE CURRENT

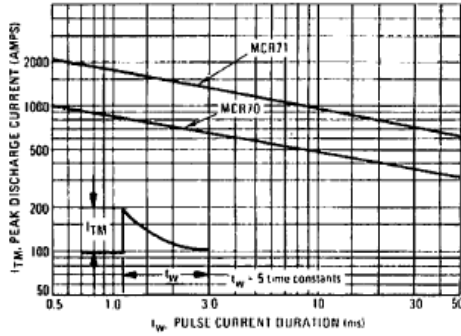


FIGURE 2 - PEAK CAPACITOR DISCHARGE CURRENT DERATING

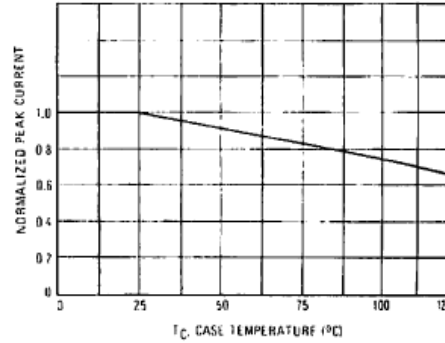


FIGURE 3 - AVERAGE CURRENT DERATING MCR70

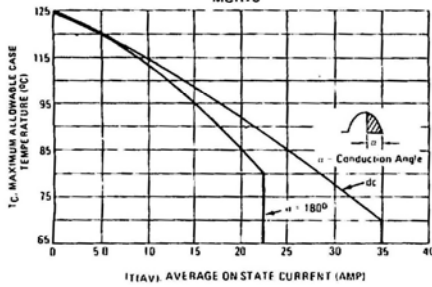


FIGURE 4 - POWER DISSIPATION MCR70

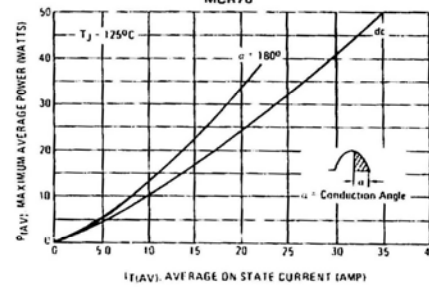


FIGURE 5 - CURRENT DERATING MCR71

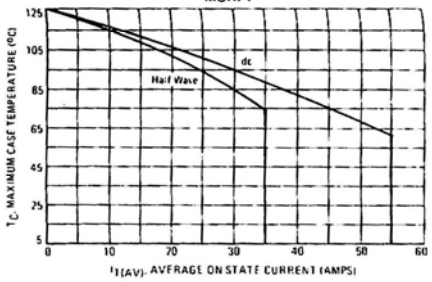


FIGURE 6 - POWER DISSIPATION MCR71

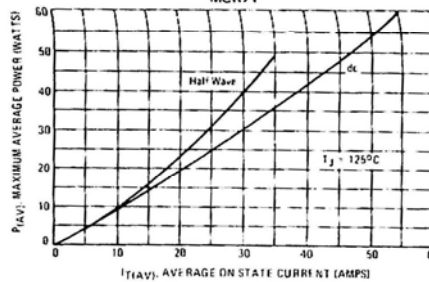
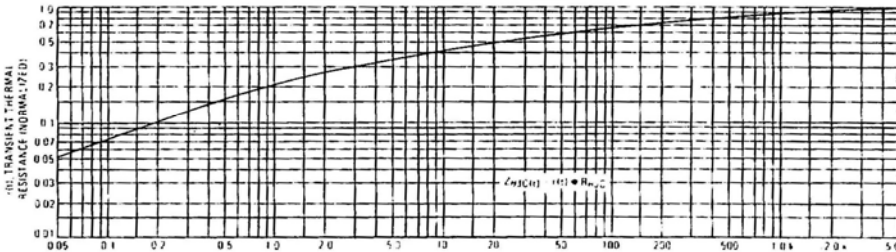


FIGURE 7 - TYPICAL THERMAL RESPONSE



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FIGURE 8 - GATE TRIGGER CURRENT

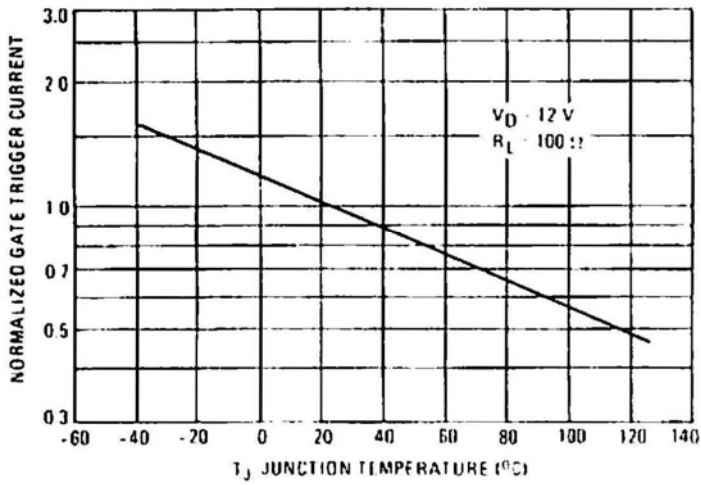


FIGURE 9 - GATE TRIGGER VOLTAGE

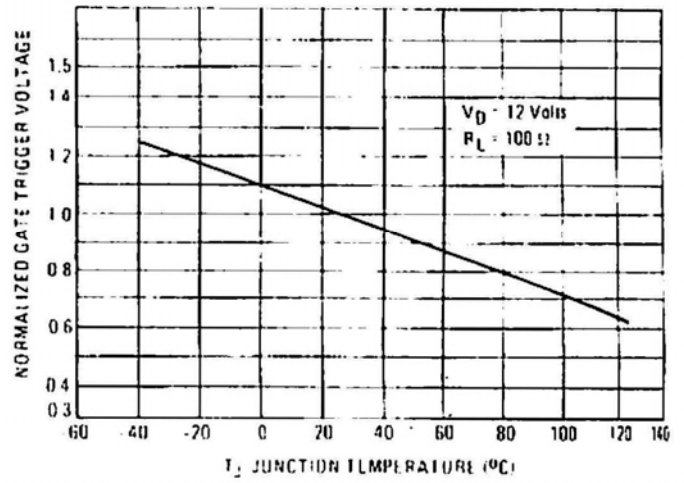


FIGURE 10 - HOLDING CURRENT

